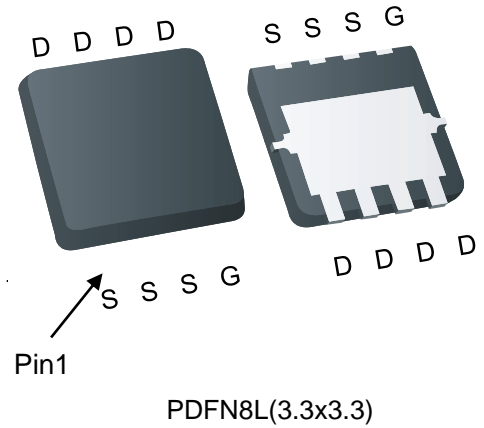


N-Channel Enhancement Mode MOSFET

Feature

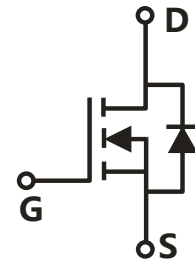
- 40V/57A
 $R_{DS(ON)} = 5.3\ m\ (\text{typ.}) @ V_{GS} = 10V$
 $R_{DS(ON)} = 7.3\ m\ (\text{typ.}) @ V_{GS} = 4.5V$
- 100% Avalanche Tested
- 100% DVDS
- Reliable and Rugged
- Halogen Free and Green Devices Available
 (RoHS Compliant)

Pin Description




Applications

- Switching application
- Li-battery protection
- DC-DC
- Motor control



Single N-Channel MOSFET

Ordering and Marking Information

HYG  060N04LS XYMXXXXX	Package Code C1: PDFN8L(3.3x3.3) Date Code XYMXXXXX
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Note: HUAYI halogen free products contain molding compounds and 100% matte tin plate Termination finish; which are fully compliant with RoHS. HUAYI halogen free products meet or exceed the halogen free requirements of IPC/JEDEC J-STD-020 for MSL classification at halogen free peak reflow temperature. HUAYI defines "Green" to mean halogen free (RoHS compliant) and halogen free (Br or Cl does not exceed 900ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500ppm by weight).

HUAYI reserves the right to make changes, corrections, enhancements, modifications, and improvements to this product and/or to this document at any time without notice.

Absolute Maximum Ratings

Symbol	Parameter	Rating	Unit
Common Ratings (Tc=25°C Unless Otherwise Noted)			
V _{DSS}	Drain-Source Voltage	40	V
V _{GSS}	Gate-Source Voltage	±20	V
T _J	Junction Temperature Range	-55 to 175	°C

HYG060N04LS1C1

Typical Operating Characteristics

Figure 1: Power Dissipation

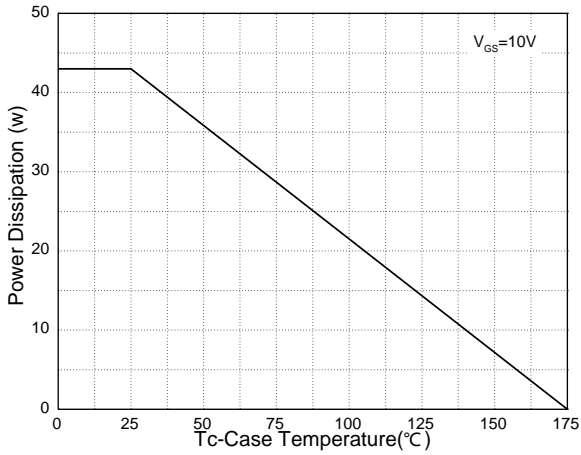


Figure 2: Drain Current

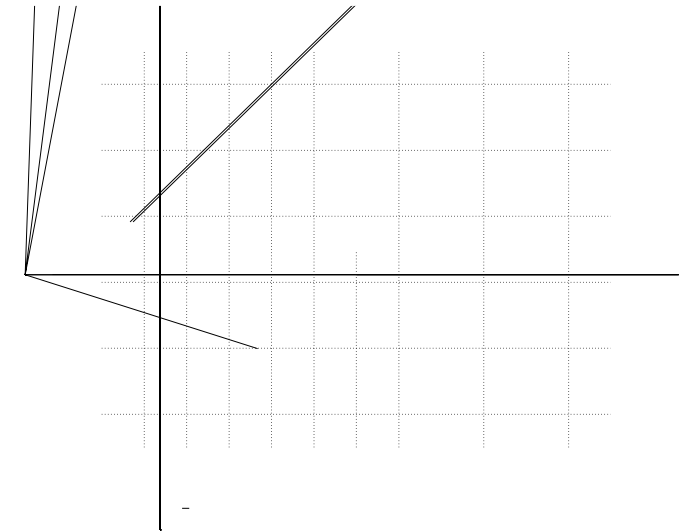


Figure 3: Safe Operation Area

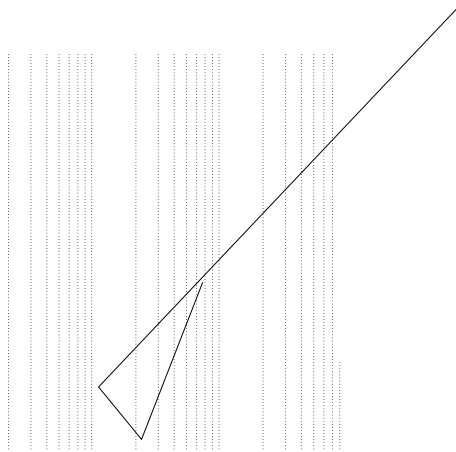


Figure 4: Thermal Transient Impedance

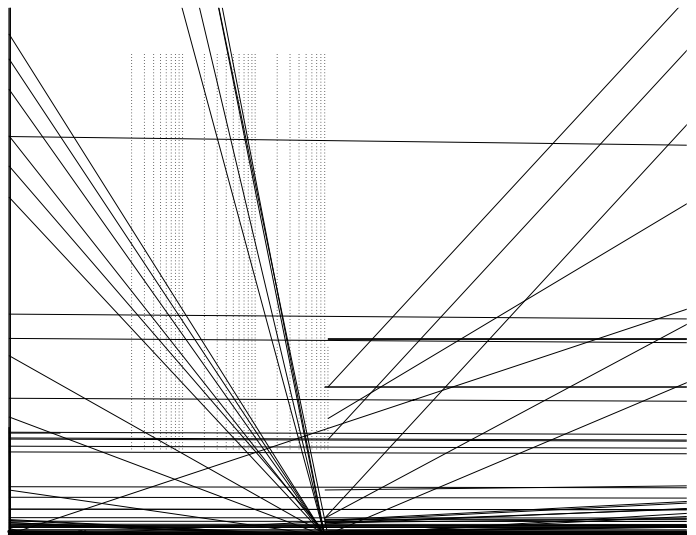
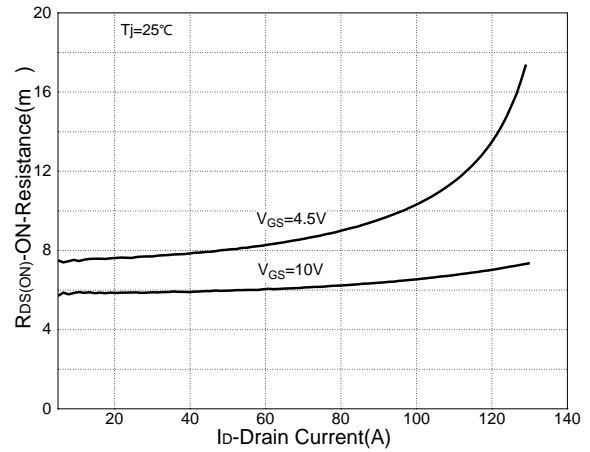


Figure 5: Output Characteristics

Figure 6: Drain-Source On Resistance



Typical Operating Characteristics(Cont.)

Figure 7: On-Resistance vs. Temperature

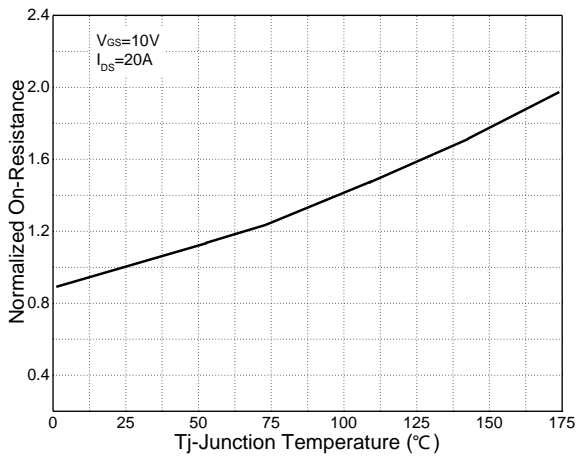


Figure 9: Capacitance Characteristics

Figure 8: Source-Drain Diode Forward

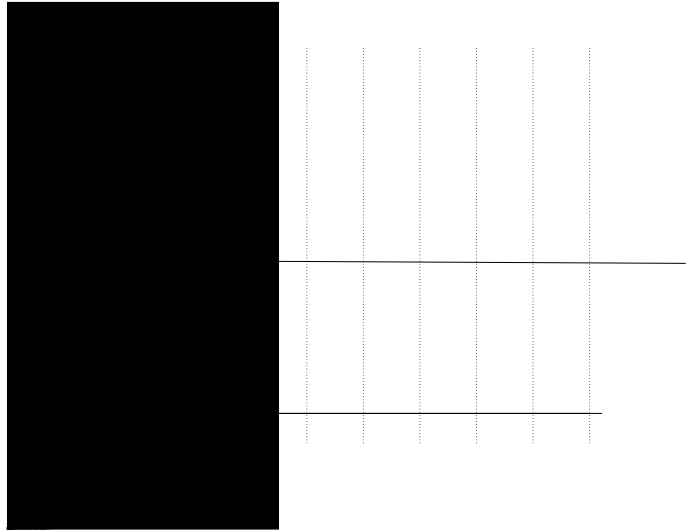
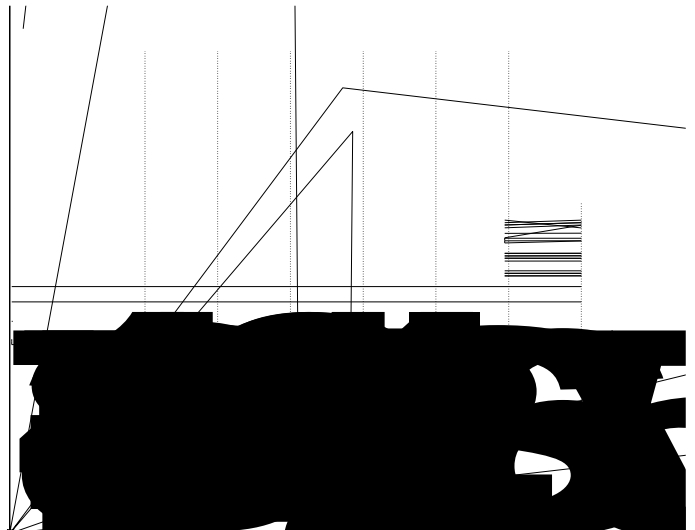
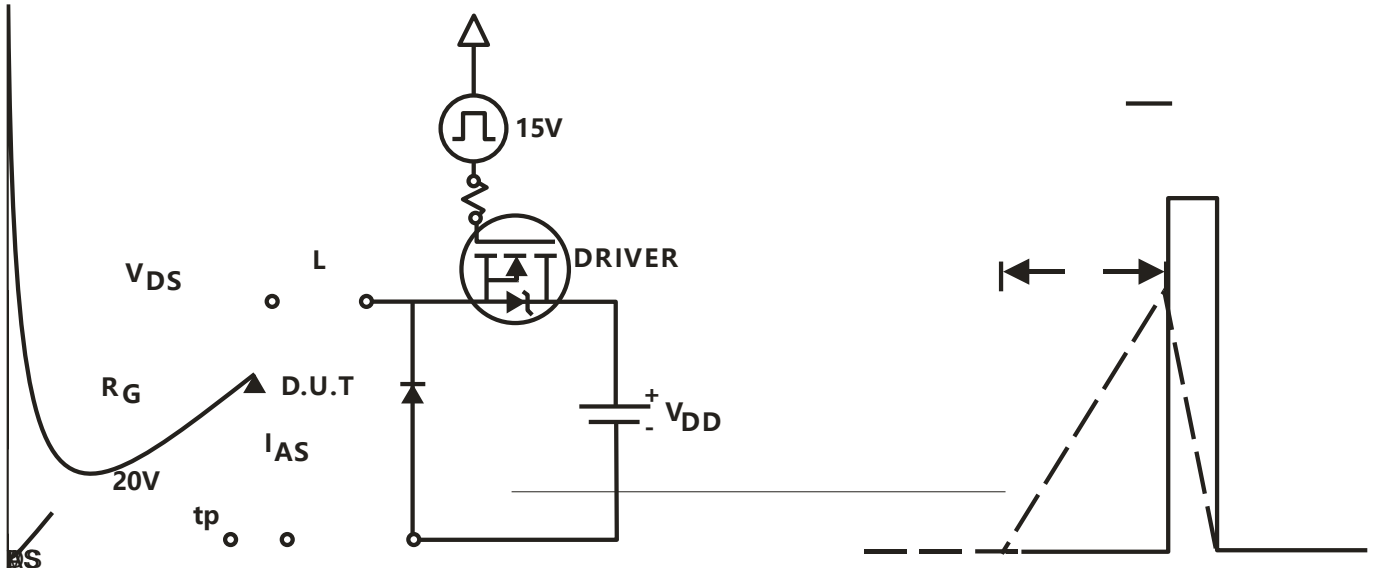


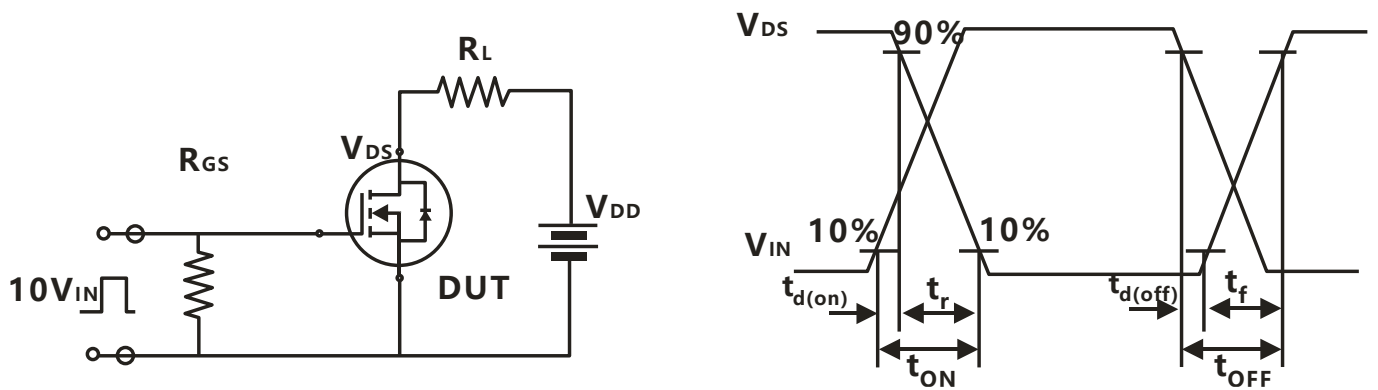
Figure 10: Gate Charge Characteristics



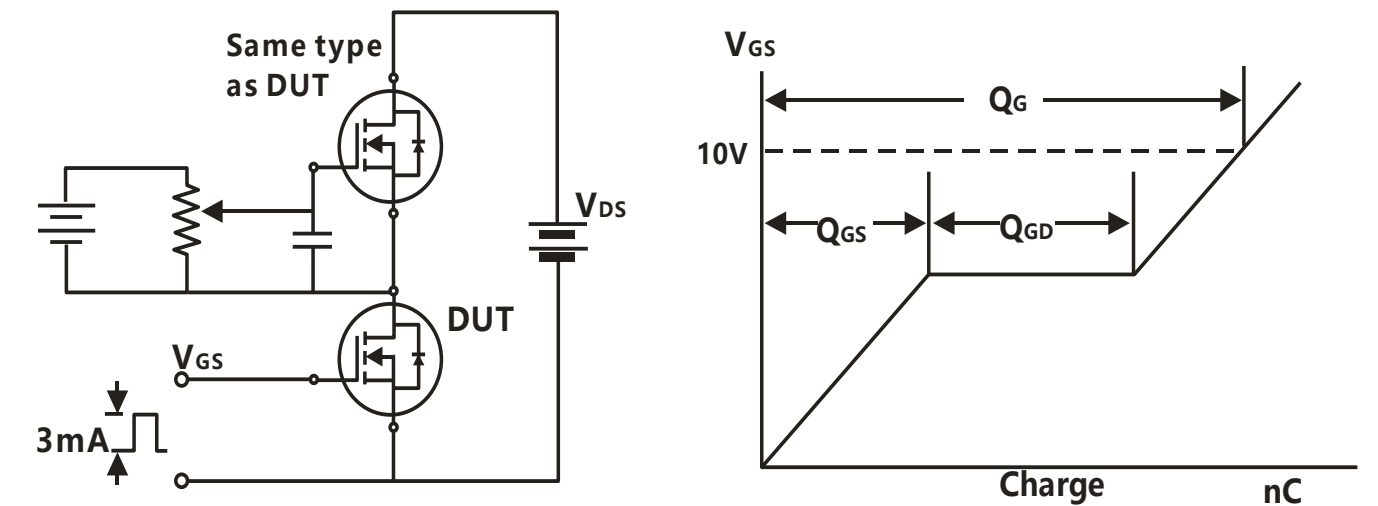
Avalanche Test Circuit



Switching Time Test Circuit



Gate Charge Test Circuit

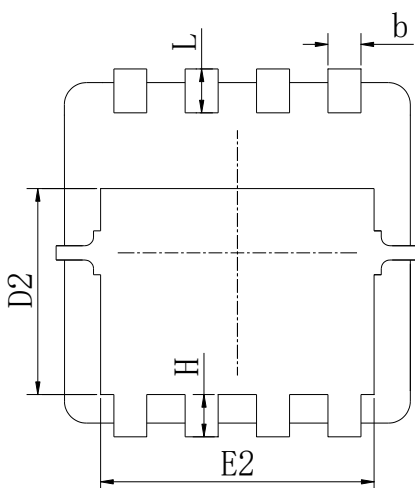
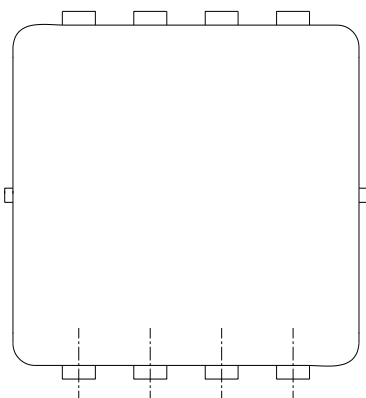


Device Per Unit

Package Type	Unit	Quantity
PDFN8L(3.3x3.3)	Reel	6500

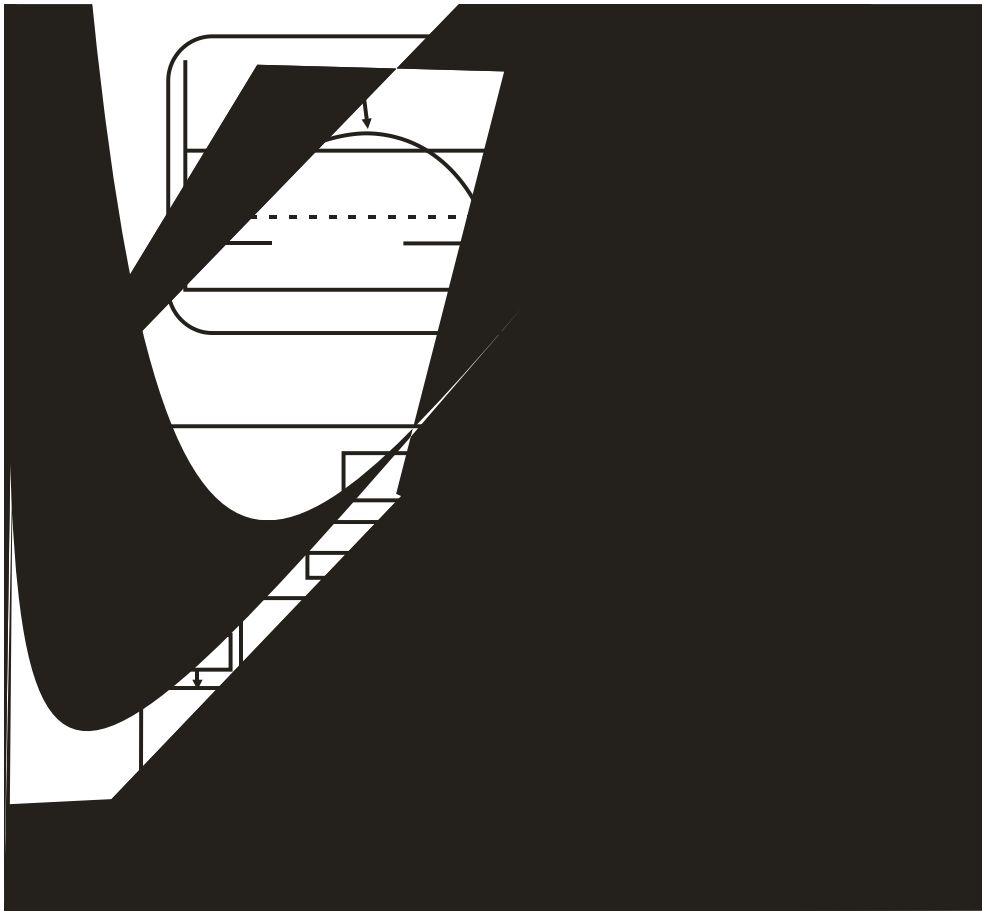
Package Information

PDFN8L(3.3x3.3)



COMMON DIMENSIONS			
SYMBOL	mm		
	MIN	NOM	MAX
A	0.70	0.75	0.80
b	0.25	0.30	0.35
c	0.10	0.15	0.25
D	3.25	3.35	3.45
D1	3.00	3.10	3.20
D2	1.78	1.88	1.98
E1	3.10	3.20	3.30
E2	2.44	2.54	2.64
e	0.65BSC		
H	0.30	0.39	0.50
L	0.30	0.40	0.50
M	\	\	0.10
*Not specified			

Classification Profile



Classification Reflow Profiles

Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Preheat & Soak		
Temperature min (T_{smin})	100 °C	150 °C
Temperature max (T_{smax})	150 °C	200 °C
Time (T_{smin} to T_{smax}) (t_s)	60-120 seconds	60-120 seconds
Average ramp-up rate (T_{smax} to T_P)	3 °C/second max.	3°C/second max.
Liquidous temperature (T_L)	183 °C	217 °C
Time at liquidous (t_l)	60-150 seconds	60-150 seconds
Peak package body Temperature (T_P)*	See Classification Temp in table 1	See Classification Temp in table 2
Time (t_p)** within 5°C of the specified classification temperature (T_c)	20** seconds	30** seconds
Average ramp-down rate (T_P to T_{smax})	6 °C/second max.	6 °C/second max.
Time 25°C to peak temperature	6 minutes max.	8 minutes max.
*Tolerance for peak profile Temperature (T_P) is defined as a supplier minimum and a user maximum.		
** Tolerance for time at peak profile temperature (t_p) is defined as a supplier minimum and a user maximum.		

Table 1.SnPb Eutectic Process – Classification Temperatures (Tc)

Package Thickness	Volume mm ³ <350	Volume mm ³ ≥350
<2.5 mm	235 °C	220 °C
2.5 mm	220 °C	220 °C

Table 2.Pb-free Process – Classification Temperatures (Tc)

Package Thickness	Volume mm ³ <350	Volume mm ³ 350-2000	Volume mm ³ ≥2000
<1.6 mm	260 °C	260 °C	260 °C
1.6 mm – 2.5 mm	260 °C	250 °C	245 °C
≥2.5 mm	250 °C	245 °C	245 °C

Reliability Test Program

Test item	Method	Description
SOLDERABILITY	JESD-22, B102	5 Sec, 245°C
HTRB	JESD-22, A108	168/500 Hrs, Bias @ 150°C
HTGB	JESD-22, A108	168 /500 Hrs, V _{gs} 100% @ 150°C
PCT	JESD-22, A102	96 Hrs, 100%RH, 2atm, 121°C
TCT	JESD-22, A104	250/500 Cycles, -55°C~150°C

Customer Service

Worldwide Sales and Service: sales@hymexa.com

Technical Support:Technology@hymexa.com

Huayi Microelectronics Co., Ltd.